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**Listing of the Claims**

1. (previously presented) A silicon nitride film formation method, comprising:
  - heating a substrate to be subjected to film formation to a substrate temperature;
  - heating a wire to a wire temperature;
  - supplying silane, ammonia, and hydrogen gases to the heating member, wherein excess hydrogen gas is supplied in an amount sufficient to form a substantially 100% conformal silicon nitride film on the substrate, wherein the conformal silicon nitride film has a highly uniform thickness providing about 100% step coverage.
2. (original) The method of claim 1, wherein the substrate temperature is in the range of about 200 - 400°C.
3. (original) The method of claim 1, wherein the wire temperature is in the range of about 1800 - 2100°C.
4. (original) The method of claim 1, further comprising conducting the silicon nitride film formation method at a pressure in the range of about 10 - 50 millitorr.
5. (previously presented) A method for forming a silicon nitride film, comprising:
  - providing a process chamber;
  - heating a substrate contained within the process chamber to a substrate temperature;
  - heating a wire contained within the process chamber to a wire temperature;
  - supplying a silicon precursor material to the process chamber;
  - supplying a nitrogen precursor material to the process chamber;
  - supplying a process gas to the process chamber in an amount sufficient to form a substantially 100% conformal silicon nitride film on the substrate, wherein the conformal silicon nitride film has a highly uniform thickness providing about 100% step coverage.

6. (original) The method of claim 5, wherein the silicon precursor material is selected from the group consisting of  $\text{SiH}_4$ ,  $\text{Si}_2\text{H}_6$ , and  $\text{SiH}_2\text{Cl}_2$ .
7. (original) The method of claim 5, wherein the nitrogen precursor material is selected from the group consisting of  $\text{N}_2$  and  $\text{NH}_3$ .
8. (original) The method of claim 5, wherein the process gas comprises hydrogen.
9. (original) The method of claim 5, wherein the substrate temperature is in the range of about 200 - 400°C.
10. (original) The method of claim 5, wherein the wire temperature is in the range of about 1800 - 2100°C.
11. (original) The method of claim 5, further comprising conducting the silicon nitride film formation method at a pressure in the range of about 10 - 50 millitorr.
12. (withdrawn) Apparatus for forming a silicon nitride film on a substrate, comprising:
  - a process chamber;
  - a substrate heater positioned within said process chamber, said substrate heater configured to receive the substrate;
  - a wire positioned within said process chamber;
  - a supply of silicon precursor material operatively associated with said process chamber;
  - a supply of nitrogen precursor material operatively associated with said process chamber; and
  - a supply of process enhancement gas operatively associated with said process chamber.
13. (withdrawn) The apparatus of claim 12, wherein the silicon precursor material is selected from the group consisting of  $\text{SiH}_4$ ,  $\text{Si}_2\text{H}_6$ , and  $\text{SiH}_2\text{Cl}_2$ .

14. (withdrawn) The apparatus of claim 12, wherein the nitrogen precursor material is selected from the group consisting of  $N_2$  and  $NH_3$ .
15. (withdrawn) The apparatus of claim 12, wherein the process gas comprises hydrogen.
16. (withdrawn) Apparatus for forming a silicon nitride film on a substrate, comprising:  
a process chamber;  
heating means positioned within said process chamber for heating the substrate to a substrate temperature;  
a wire positioned within said process chamber;  
means for providing a silicon precursor material to said process chamber;  
means for providing a nitrogen precursor material to said process chamber; and  
means for supplying a process enhancement gas to said process chamber.
17. (withdrawn) The apparatus of claim 16, wherein said means for providing a silicon precursor material to said process chamber comprises means for providing  $SiH_4$  to said process chamber.
18. (withdrawn) The apparatus of claim 16, wherein said means for providing a nitrogen precursor material to said process chamber comprises means for providing  $NH_3$  to said process chamber.
19. (withdrawn) The apparatus of claim 16, wherein said means for supplying a process enhancement gas to said process chamber comprises means for providing  $H_2$  to said process chamber.
20. (previously presented) The method of claim 1, wherein the conformal silicon nitride film has a highly uniform thickness.

21. (previously presented) The method of claim 1, wherein the conformal silicon nitride film has a highly uniform thickness on all side portions.
22. (previously presented) The method of claim 1, wherein the conformal silicon nitride film exhibits step coverage of very small-scale features on the substrate.
23. (canceled)
24. (previously presented) The method of claim 5, wherein the conformal silicon nitride film has a highly uniform thickness.
25. (previously presented) The method of claim 5, wherein the conformal silicon nitride film has a highly uniform thickness on top, bottom, and side portions.
26. (previously presented) The method of claim 5, wherein the conformal silicon nitride film exhibits step coverage of very small-scale features on the substrate.
27. (canceled)